



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Diodes

1SS401 Schottky DIODES

FEATURES

Low forward voltage : $V_F=0.38V(\text{typ.})$

Low reverse current : $I_R=50\mu A(\text{max})$

Small total capacitance : $C_T=46\text{pF}(\text{typ.})$

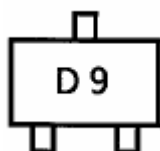
SOT-323



1. ANODE

2. NC

3. CATHODE



MARKING:

Maximum Ratings @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	25	V
Peak Repetitive Peak reverse voltage	V_{RRM}	20	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	700	mA
Average Rectified Output Current	I_O	300	mA
Power Dissipation	P_d	100	mW
Junction temperature	T_J	125	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55-125	$^\circ\text{C}$

Electrical Characteristics @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	20			V	$I_R=100\mu A$
Forward voltage	V_{F1}		0.16		V	$I_F=1\text{mA}$
	V_{F2}		0.22		V	$I_F=10\text{mA}$
	V_{F3}		0.38	0.45	V	$I_F=300\text{mA}$
Reverse current	I_R			50	μA	$V_R=20\text{V}$
Capacitance between terminals	C_T		46		pF	$V_R=0, f=1\text{MHz}$

Typical Characteristics

ISS401

